

30 V, N-channel Trench MOSFET

26 January 2021

#### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Low threshold voltage
- Extended temperature range T<sub>i</sub> = 175 °C
- Trench MOSFET technology
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (Class H1C)
- AEC-Q101 qualified

#### 3. Applications

- DC to DC conversion
- High-speed line driver
- Low-side load switch
- Switching circuits

#### 4. Quick reference data

| Table 1. Quick refere | nce data |
|-----------------------|----------|
|-----------------------|----------|

| -                 |                                     |   |     |     |     |      |
|-------------------|-------------------------------------|---|-----|-----|-----|------|
| Symbol            | Parameter                           | Conditions  | Min | Тур | Max | Unit |
| V <sub>DS</sub>   | drain-source voltage                | T <sub>j</sub> = 25 °C  | -   | -   | 30  | V    |
| V <sub>GS</sub>   | gate-source voltage                 |   | -12 | -   | 12  | V    |
| I <sub>D</sub>    | drain current                       | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C                       | -   | -   | 3.4 | А    |
| Static characte   | eristics                            |   |     |     |     |      |
| R <sub>DSon</sub> | drain-source on-state<br>resistance | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.4 A; T <sub>j</sub> = 25 °C | -   | 48  | 60  | mΩ   |

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### 5. Pinning information

| Table 2. Pinning information |        |             |                    |                     |  |  |  |
|------------------------------|--------|-------------|--------------------|---------------------|--|--|--|
| Pin                          | Symbol | Description | Simplified outline | Graphic symbol      |  |  |  |
| 1                            | G      | gate        | 3                  | D                   |  |  |  |
| 2                            | S      | source      |                    |                     |  |  |  |
| 3                            | D      | drain       |                    | G<br>S<br>017aaa255 |  |  |  |

### 6. Ordering information

| Table 3. Ordering information |         |  |         |  |  |  |
|-------------------------------|---------|--|---------|--|--|--|
| Type number                   | Package |  |         |  |  |  |
|                               | Name    | Description  | Version |  |  |  |
| PMV50XNEA                     |         | plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body | SOT23   |  |  |  |

### 7. Marking

#### Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| PMV50XNEA   | XJ%             |

[1] % = placeholder for manufacturing site code

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### 8. Limiting values

#### Table 5. Limiting values

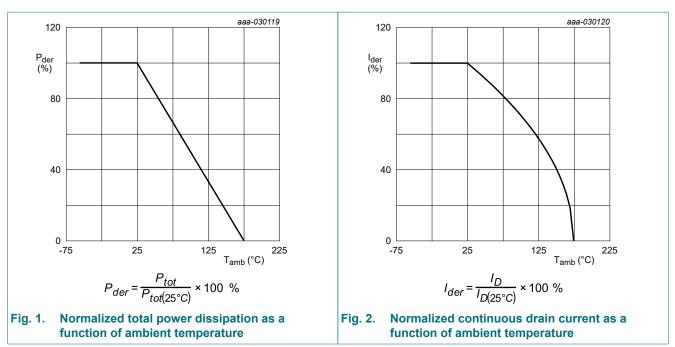
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                          | Parameter  | Conditions  |     | Min | Max  | Unit |
|---------------------------------|--|---|-----|-----|------|------|
| V <sub>DS</sub>                 | drain-source voltage                             | T <sub>j</sub> = 25 °C  |     | -   | 30   | V    |
| V <sub>GS</sub>                 | gate-source voltage                              |   |     | -12 | 12   | V    |
| I <sub>D</sub>                  | drain current                                    | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C                                     |     | -   | 3.4  | А    |
|                                 |  | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C                                    |     | -   | 2.2  | Α    |
| I <sub>DM</sub>                 | peak drain current                               | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$                                 |     | -   | 14   | А    |
| P <sub>tot</sub> total power of | total power dissipation                          | T <sub>amb</sub> = 25 °C  | [1] | -   | 590  | mW   |
|                                 |  |   | [2] | -   | 1.3  | W    |
|                                 |  | T <sub>sp</sub> = 25 °C   |     | -   | 5.6  | W    |
| Tj                              | junction temperature                             |   |     | -55 | 175  | °C   |
| T <sub>amb</sub>                | ambient temperature                              |   |     | -55 | 175  | °C   |
| T <sub>stg</sub>                | storage temperature                              |   |     | -65 | 175  | °C   |
| Source-drai                     | n diode  |   |     | I   |      |      |
| Is                              | source current                                   | T <sub>amb</sub> = 25 °C  | [2] | -   | 1.3  | А    |
| ESD maxim                       | um rating  |   |     | I   |      |      |
| V <sub>ESD</sub>                | electrostatic discharge voltage                  | НВМ   | [3] | -   | 1000 | V    |
| Avalanche r                     | uggedness  |   |     |     |      |      |
| E <sub>DS(AL)S</sub>            | non-repetitive drain-<br>source avalanche energy | T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 0.4 A; DUT in<br>avalanche (unclamped) |     | -   | 6    | mJ   |
| 20((.12)0                       |  |   |     |     |      |      |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

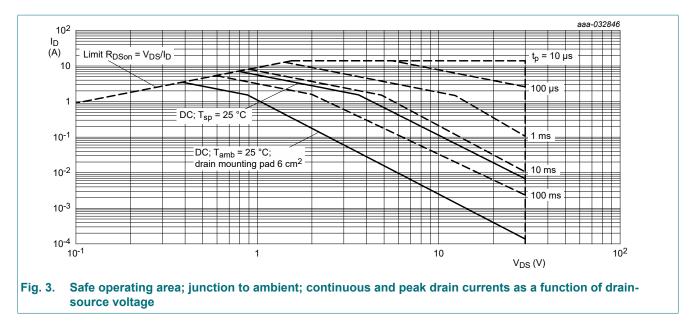
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

[3] Measures between all pins.



**Product data sheet** 

#### 30 V, N-channel Trench MOSFET

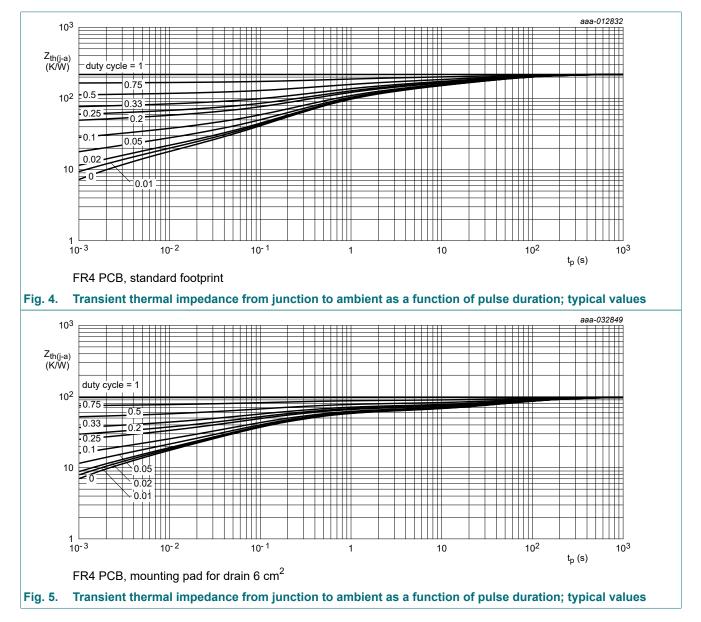


#### 9. Thermal characteristics

| Symbol                                       | Parameter  | Conditions |     | Min | Тур | Max | Unit |
|--|--|------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub> thermal resistance from | in free air                                      | [1]        | -   | 217 | 255 | K/W |      |
|  | junction to ambient                              |            | [2] | -   | 97  | 112 | K/W  |
| R <sub>th(j-sp)</sub>                        | thermal resistance from junction to solder point |            |     | -   | 23  | 27  | K/W  |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

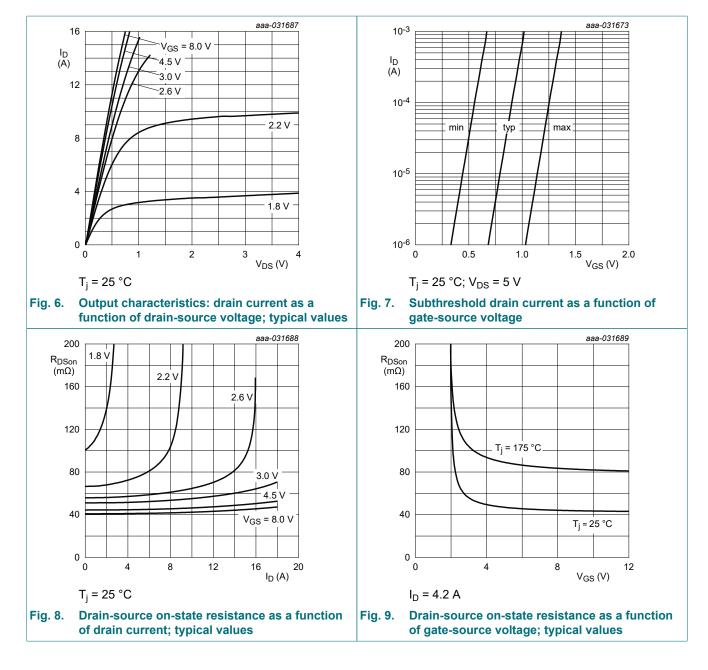
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



### **10. Characteristics**

| Symbol               | Parameter   | Conditions   | Min | Тур | Max  | Unit |
|----------------------|---|--|-----|-----|------|------|
| Static chara         | cteristics  |  |     |     |      | _    |
| V <sub>(BR)DSS</sub> | drain-source<br>breakdown voltage                                     | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C             | 30  | -   | -    | V    |
| V <sub>GSth</sub>    | gate-source threshold voltage   | I <sub>D</sub> = 250 μA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C | 0.6 | 0.9 | 1.25 | V    |
| I <sub>DSS</sub>     | drain leakage current   | V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C              | -   | -   | 1    | μA   |
| I <sub>GSS</sub>     | gate leakage current  | V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C              | -   | -   | 10   | μA   |
|                      |   | V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C             | -   | -   | -10  | μA   |
|                      |   | V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C             | -   | -   | 2    | μA   |
|                      |   | $V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                   | -   | -   | -2   | μA   |
| R <sub>DSon</sub>    | drain-source on-state   | V <sub>GS</sub> = 8 V; I <sub>D</sub> = 3.4 A; T <sub>j</sub> = 25 °C              | -   | 45  | 57   | mΩ   |
| resistance           | resistance  | V <sub>GS</sub> = 8 V; I <sub>D</sub> = 3.4 A; T <sub>j</sub> = 175 °C             | -   | 86  | 110  | mΩ   |
|                      |   | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.4 A; T <sub>j</sub> = 25 °C            | -   | 48  | 60   | mΩ   |
|                      | V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 1 A; T <sub>j</sub> = 25 °C | -  | 66  | 102 | mΩ   |      |
| 9 <sub>fs</sub>      | forward<br>transconductance   | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 3.4 A; T <sub>j</sub> = 25 °C             | -   | 6   | -    | S    |
| R <sub>G</sub>       | gate resistance   | f = 1 MHz  | -   | 1.2 | -    | Ω    |
| Dynamic ch           | aracteristics   |  |     |     |      |      |
| Q <sub>G(tot)</sub>  | total gate charge   | V <sub>DS</sub> = 15 V; I <sub>D</sub> = 4 A; V <sub>GS</sub> = 4.5 V;             | -   | 3.3 | 5    | nC   |
| Q <sub>GS</sub>      | gate-source charge  | T <sub>j</sub> = 25 °C   | -   | 0.6 | -    | nC   |
| Q <sub>GD</sub>      | gate-drain charge   |  | -   | 1   | -    | nC   |
| C <sub>iss</sub>     | input capacitance   | V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                          | -   | 296 | -    | pF   |
| C <sub>oss</sub>     | output capacitance  | T <sub>j</sub> = 25 °C   | -   | 28  | -    | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance  |  | -   | 22  | -    | pF   |
| t <sub>d(on)</sub>   | turn-on delay time  | V <sub>DS</sub> = 15 V; I <sub>D</sub> = 4 A; V <sub>GS</sub> = 4.5 V;             | -   | 2   | -    | ns   |
| t <sub>r</sub>       | rise time   | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$   | -   | 4   | -    | ns   |
| t <sub>d(off)</sub>  | turn-off delay time   |  | -   | 7   | -    | ns   |
| t <sub>f</sub>       | fall time   |  | -   | 2   | -    | ns   |
| Source-drai          | n diode   |  |     |     |      | _    |
| V <sub>SD</sub>      | source-drain voltage  | I <sub>S</sub> = 1.3 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C              | -   | 0.8 | 1.2  | V    |
| t <sub>rr</sub>      | reverse recovery time   | I <sub>S</sub> = 2 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;      | -   | 6   | -    | ns   |
| Q <sub>r</sub>       | recovered charge  | V <sub>DS</sub> = 15 V; T <sub>j</sub> = 25 °C                                     | -   | 1   | -    | nC   |

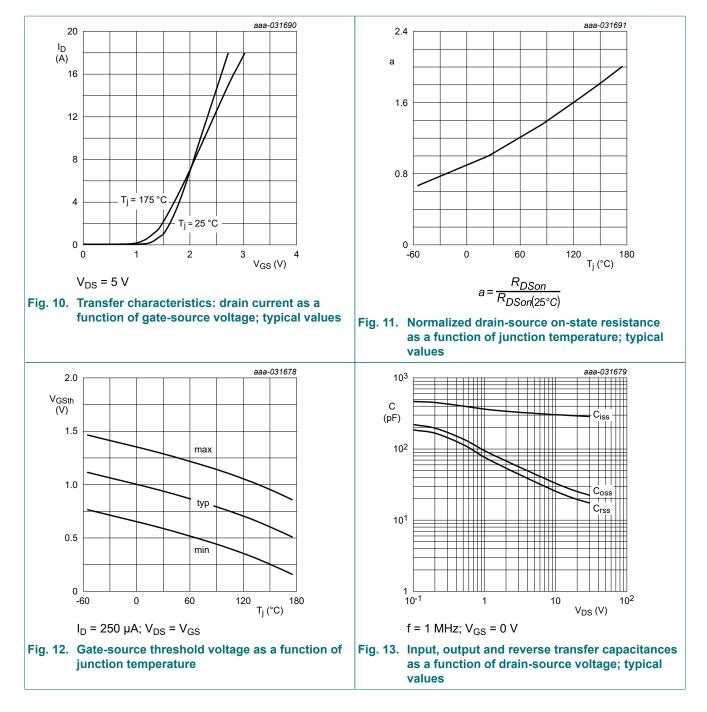
#### 30 V, N-channel Trench MOSFET



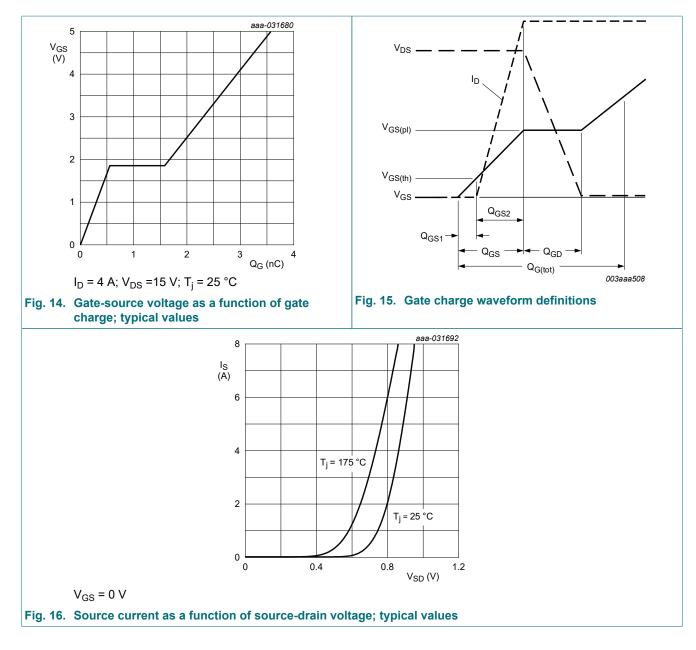
**Product data sheet** 

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#### 30 V, N-channel Trench MOSFET

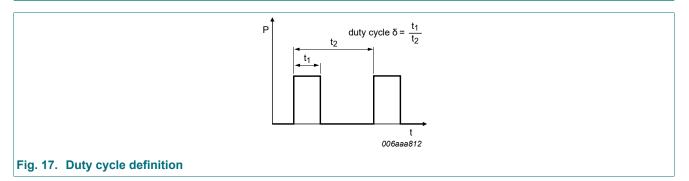


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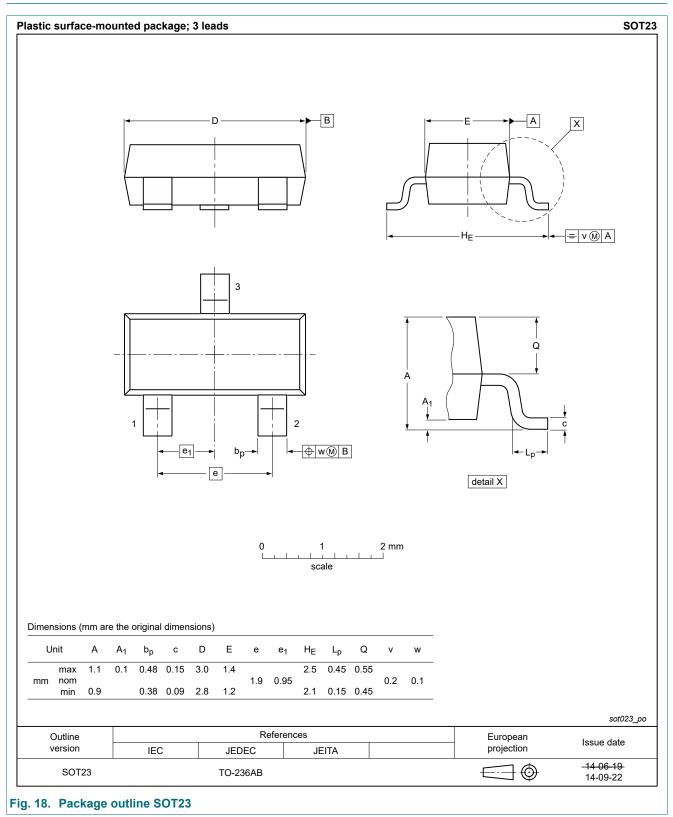
### **11. Test information**



#### **Quality information**

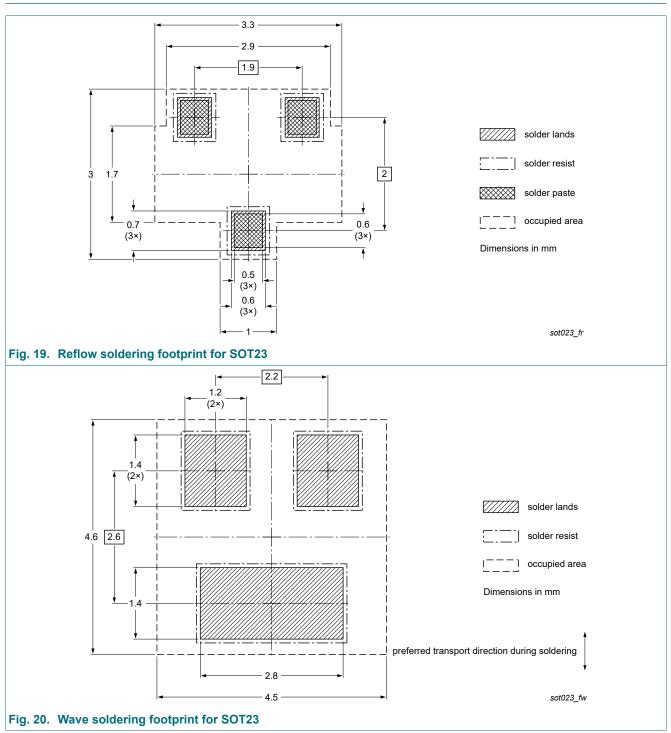
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### 12. Package outline



#### 30 V, N-channel Trench MOSFET

#### 13. Soldering



### 14. Revision history

| Table 8. Revision history |              |                    |               |            |  |  |
|---------------------------|--------------|--------------------|---------------|------------|--|--|
| Data sheet ID             | Release date | Data sheet status  | Change notice | Supersedes |  |  |
| PMV50XNEA v.1             | 20210126     | Product data sheet | -             | -          |  |  |

### 15. Legal information

#### **Data sheet status**

| Document status [1][2]            | Product<br>status [3] | Definition  |
|-----------------------------------|-----------------------|---|
| Objective [short]<br>data sheet   | Development           | This document contains data from<br>the objective specification for<br>product development. |
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